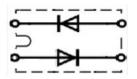




Ultrafast High Voltage Diode

FEATURES

- · High surge current capability
- · Wide current range
- High voltage ratings up to 1200V
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

 Be suitable in motor control circuitries, or in the primary of SMPS as snubber, clamping or demagnetizing diodes. They are also suitable for secondary of SMPS as high voltage rectifier diodes.



ABSOLUTE MAXIMUM RATINGS

T	1		1	
PARAMETER	CONDITIONS		VALUE	UNIT
Repetitive Peak Reverse Voltage			1200	V
Average Forward Current			2*45	А
RMS Forward Current	$T_{VJ} = T_{VJM}$		70	А
	t=10ms(50Hz),sine	- T _{VJ} =45°C - T _{VJ} =150°C -	200	- A
	t=8.3ms(60Hz),sine		210	
Surge Forward Current	t=10ms(50Hz),sine		185	
	t=8.3ms(60Hz),sine		195	
	t=10ms(50Hz),sine		200	- KA₂s
I ² t for fusing	t=8.3ms(60Hz),sine	1 _{VJ} =45 C	180	
	t=10ms(50Hz),sine		170	
	t=8.3ms(60Hz),sine		160	
Junction Temperature			-40~150	$^{\circ}$
Storage Temperature Range			-40~150	°C
	Repetitive Peak Reverse Voltage Average Forward Current RMS Forward Current Surge Forward Current I²t for fusing Junction Temperature	Repetitive Peak Reverse Voltage Average Forward Current RMS Forward Current	Repetitive Peak Reverse Voltage Average Forward Current T_{VJ} = T_{VJM}	Repetitive Peak Reverse Voltage

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Ultrafast High Voltage Diode

THERMAL CHARACTERISTICS

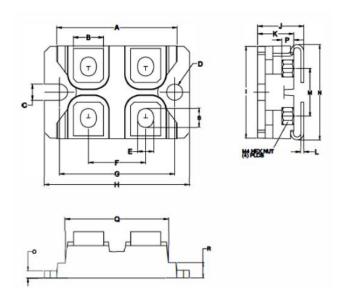
SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case		°C/W

ELECTRICAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
I _R	Reverse Recovery current	$V_R = V_{RRM}$	0.75	mA
V _{FM}	Forward Voltage drop	I _F = 30A, T _J = 150℃	2.2	V
t _{rr}	Reverse Recovery time	$I_F = 1 \text{ A}$; -di/dt = 100 A/ μ s; $V_R = 30 \text{ V}$; $T_{VJ} = 25^{\circ}\text{C}$	60	ns

PACKAGE OUTLINE

Dimensions in mm (1mm = 0.0394")



SOT-227 Package Outline

DIM	MILLIMETER		INCHES		
	MIN	MAX	MIN	MAX	
A	31.40	31.60	1.236	1.244	
В	7.70	8.10	0.303	0.319	
C	4.20	4.40	0.165	0.173	
D	4.20	4.40	0.165	0.173	
E	4.10	4.30	0.161	0.169	
F	14.90	15.10	0.587	0.594	
G	30.10	30.20	1.165	1.189	
н	38.00	38.30	1.496	1.507	
1	23.80	24.20	0.937	0.953	
J	12.20	12.70	0.480	0.500	
K	9.40	9.60	0.370	0.378	
L	0.75	0.85	0.030	0.033	
M	1240	12.60	0.488	0.496	
N	24.50	25.40	0.964	1.000	
0	1.90	2.10	0.075	0.083	
P	3.10	3.20	0.122	0.126	
Q	26.60	27.00	1.063	1.079	
R	3.80	4.20	0.150	0.165	
S	5.10	5.40	0.205	0.213	

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